NL17SZ07E

Single Non-Inverting Buffer with Open Drain Output

The NL17SZ07E is a high performance single non−inverting buffer with open drain outputs operating from a 1.65 to 5.5 V supply.

The Output stage is open drain with Over Voltage Tolerance. This allows the NL17SZ07E to be used to interface 5.0 V circuits to circuits of any voltage between 0 and +5.5 V.

Features

- Tiny SOT−353 Package
- Extremely High Speed: t_{PD} 2.5 ns (typical) at V_{CC} = 5 V
- Designed for 1.65 V to 5.5 V V_{CC} Operation, CMOS Compatible
- Over Voltage Tolerant Inputs V_{IN} may be Between 0 and 5.5 V for V_{CC} Between 0.5 and 5.5 V
- TTL Compatible − Interface Capability with 5.0 V TTL Logic with V_{CC} = 2.7 V to 3.6 V
- LVCMOS Compatible
- 24 mA Output Sink Capability, Pullup may be between 0 and 5.5 V
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 20
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant
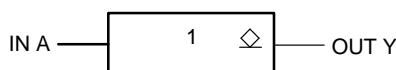
ON Semiconductor®

MARKING DIAGRAMS

SC−88A / SOT−353 / SC−70
DF SUFFIX
CASE 419A

L7 M
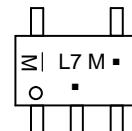
L7 = Specific Device Marking
M = Date Code*
■ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	NC
2	IN A
3	GND
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Input	Output
A	**Y**
L	L
H	Z

Figure 1. Pinout

Figure 2. Logic Symbol

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NL17SZ07E

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_I	DC Input Voltage		−0.5 to +6.5	V
	DC Output Voltage	Active Mode, LOW State (Note 1) Tri−State Mode Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
P_D	Power Dissipation in Still Air		186	mW
θ_{JA}	Thermal Resistance		350	°C/W
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
ESD	ESD Classification	Human Body Model (Note 2) Charged Device Model (Note 3)	4000 1000	V V
$I_{Latch−Up}$	Latch−Up Performance	Above V_{CC} and Below GND at 85°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A, rated to EIA/JESD22−A114−B.
3. Tested to JESD22−C101−A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage		0	5.5	V
	Output Voltage	Active Mode, LOW State Tri–State Mode Power–Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 5.5 5.5	
T_A	Operating Free–Air Temperature		−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ±0.2 V V_{CC} = 3.0 V ±0.3 V V_{CC} = 5.0 V ±0.5 V	0 0 0	20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High–Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V_{CC} 0.7 V_{CC}			0.75 V_{CC} 0.7 V_{CC}		V
V_{IL}	Low–Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.25 V_{CC} 0.3 V_{CC}		0.25 V_{CC} 0.3 V_{CC}	V
I_{LKG}	Z–State Output Leakage Current	V_{IN} = V_{IH} V_{OUT} = V_{CC} or GND	2.3 to 5.5			±5.0		±10.0	μA
V_{OL}	Low–Level Output Voltage V_{IN} = V_{IL}	I_{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I_{OL} = 4 mA	1.65		0.08	0.24		0.24	
		I_{OL} = 8 mA	2.3		0.20	0.3		0.3	
		I_{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I_{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I_{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I_{OL} = 32 mA	4.5		0.42	0.55		0.55	
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	1.65 to 5.5			±0.1		±1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0			1		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = 5.5 V or GND	5.5			1		10	μA
I_{CCT}	Quiescent Supply Current	V_{IN} = 3.0 V	3.6			10		100	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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AC ELECTRICAL CHARACTERISTICS $t_R = t_F = 2.5$ ns

Symbol	Parameter	Condition	V_{CC} (V)	$T_A = 25°C$			$-55°C \leq T_A \leq 125°C$		Unit
				Min	Typ	Max	Min	Max	
t_{PZL}	Propagation Delay (Figure 3 and 4)	$R_L = R_1 = 500\ \Omega$, $C_L = 50$ pF	1.8 ± 0.15		5.3	9.0		9.5	ns
			2.5 ± 0.2		3.7	6.1		6.5	
			3.3 ± 0.3		2.9	5.6		6.0	
			5.0 ± 0.5		2.3	4.4		4.8	
t_{PLZ}	Propagation Delay (Figure 3 and 4)	$R_L = R_1 = 500\ \Omega$, $C_L = 50$ pF	1.8 ± 0.15		5.3	9.0		9.5	ns
			2.5 ± 0.2		2.8	6.1		6.5	
			3.3 ± 0.3		2.1	5.6		6.0	
			5.0 ± 0.5		1.4	4.4		4.8	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	$V_{CC} = 5.5$ V, $V_I = 0$ V or V_{CC}	> 2.5	pF
C_{OUT}	Output Capacitance	$V_{CC} = 5.5$ V, $V_I = 0$ V or V_{CC}	4.0	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC} = 5.5$ V, $V_I = 0$ V or V_{CC}	4.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.
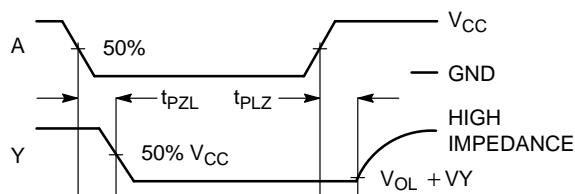
$V_{CC} = 1.8 \pm 0.15$ V or 2.5 ± 0.2 V, VY = 0.15 V
$V_{CC} = 3.3 \pm 0.3$ V or 5.0 ± 0.5 V, VY = 0.30 V

Figure 3. Switching Waveforms
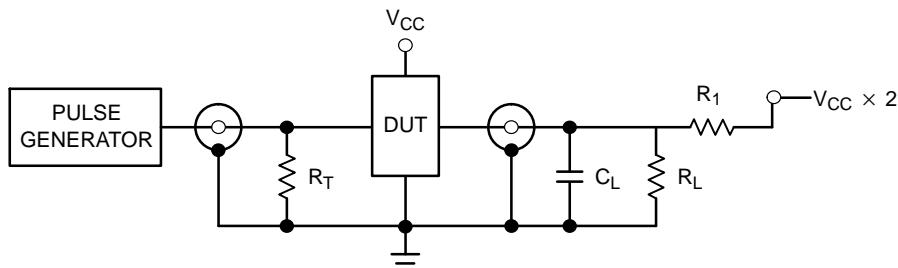
$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

DEVICE ORDERING INFORMATION

Device	Package	Shipping†
NL17SZ07EDFT2G	SOT−353/SC70−5/SC−88A (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NL17SZ07E

PACKAGE DIMENSIONS

**SC−88A (SC−70−5/SOT−353)**
CASE 419A−02
ISSUE L

A
G

5   4

S   **−B−**

1   2   3

| D 5 PL | ⊕ | 0.2 (0.008) Ⓜ | B Ⓜ |
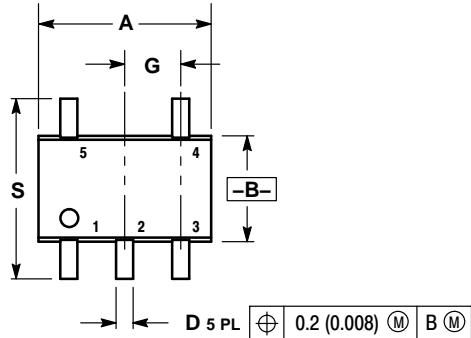
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

N

C

J

H   **K**

SOLDER FOOTPRINT*

0.50 / 0.0197

0.65 / 0.025

0.65 / 0.025

0.40 / 0.0157

1.9 / 0.0748

SCALE 20:1   (mm / inches)
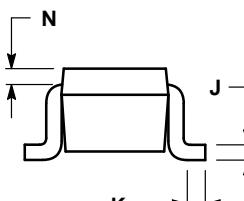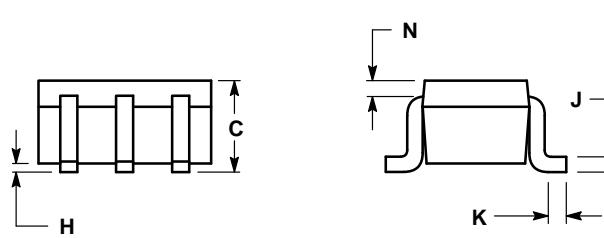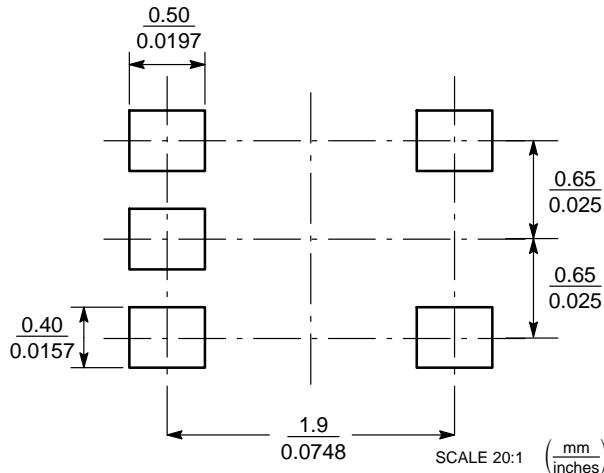
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

◊   **NL17SZ07E/D**